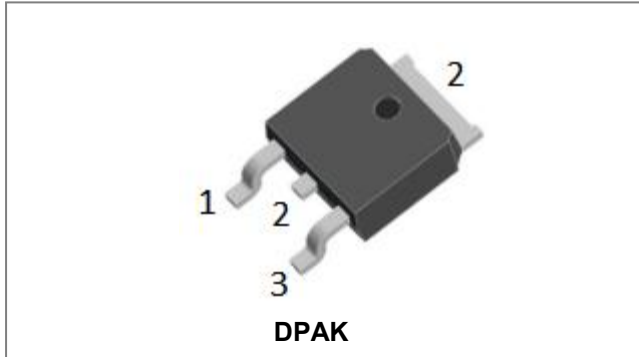


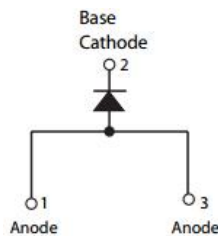
SDURD1560 ULTRAFAST RECTIFIER



Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- This is a Pb – free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	600	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_c=100^\circ\text{C}$, rectangular wave form	15	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3ms, Half Sine pulse	160	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@15A, Pulse, $T_J = 25^\circ\text{C}$	1.6	1.7	V
	V_{F2}	@15A, Pulse, $T_J = 125^\circ\text{C}$	-	1.5	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R, T_J = 25^\circ\text{C}$	0.4	10	μA
	I_{R2}	@ $V_R = \text{rated } V_R, T_J = 125^\circ\text{C}$	-	1000	μA
Reverse Recovery Time	T_{rr1}	$I_F=500\text{mA}, I_R=1\text{A}, \text{and } I_m=250\text{mA}$	30	50	ns

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	DC operation	5	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

Ratings and Characteristics Curves

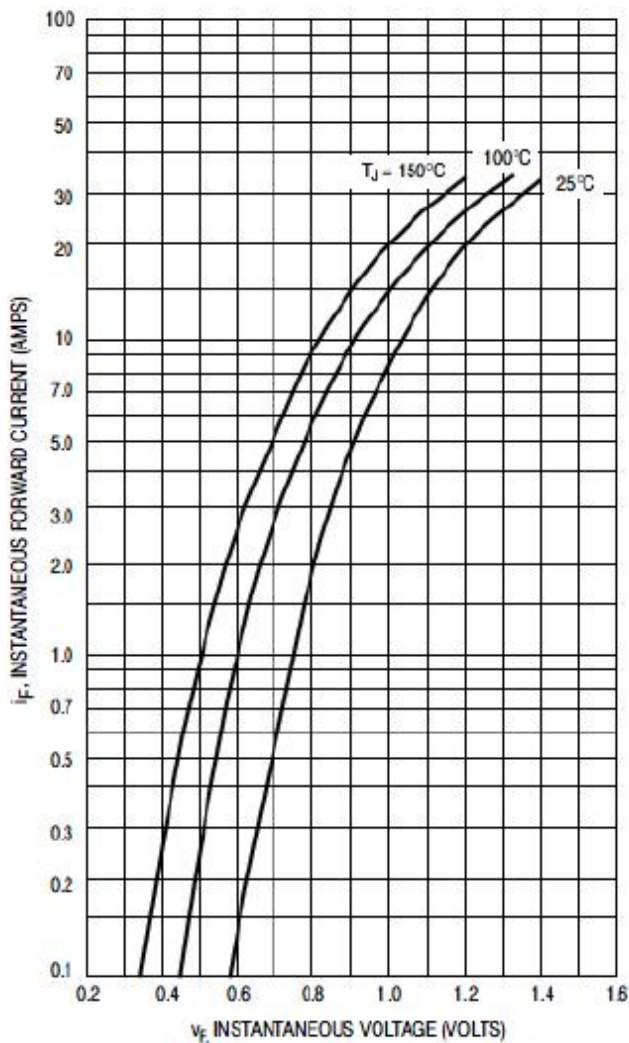


Figure 6. Typical Forward Voltage

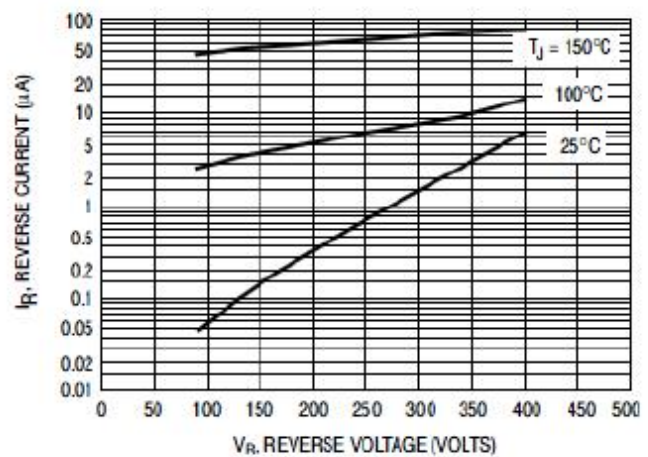


Figure 7. Typical Reverse Current

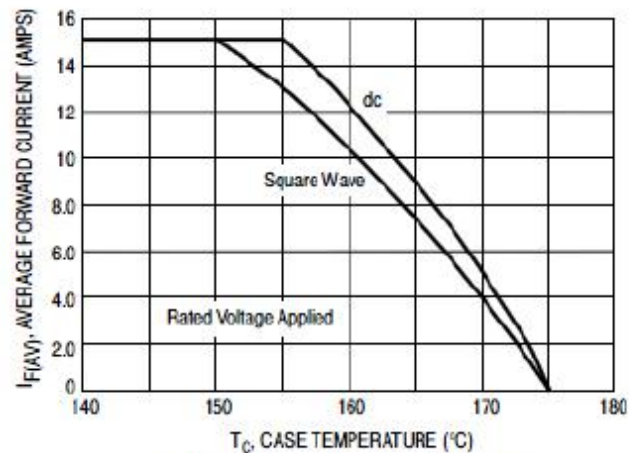
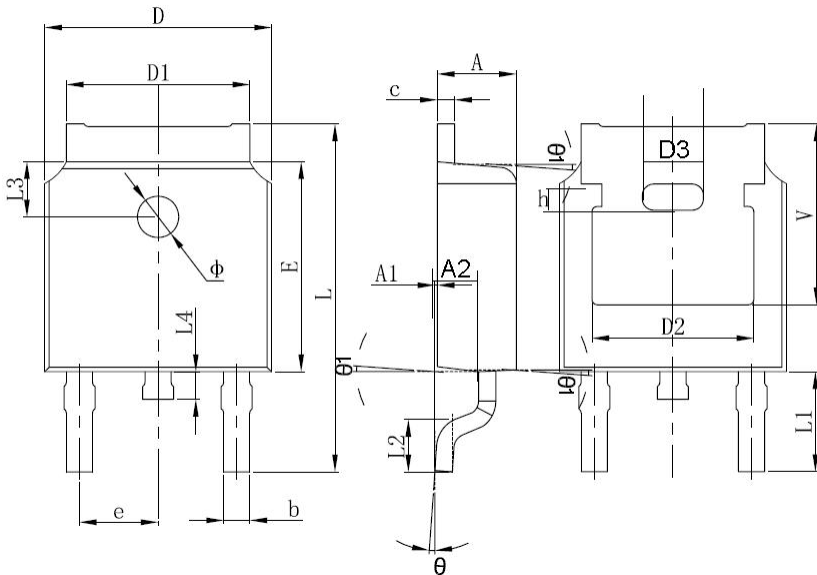


Figure 8. Current Derating, Case

Mechanical Dimensions DPAK


SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.40	0.087	0.094
A1	0.00	0.127	0.000	0.005
b	0.66	0.86	0.026	0.034
c	0.46	0.60	0.018	0.024
D	6.50	6.70	0.256	0.264
D1	5.13	5.46	0.202	0.215
D2	4.83 REF.		0.190 REF.	
E	6.00	6.20	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.70	10.40	0.381	0.409
L1	2.90 REF.		0.144 REF.	
L2	1.40	1.70	0.055	0.067
L3	1.60 REF.		0.063 REF.	
L4	0.60	1.00	0.024	0.039
Φ	1.10	1.30	0.043	0.051
Θ	0°	8°	0°	8°
h	0.00	0.30	0.000	0.012
V	5.35 REF.		0.211 REF.	

Ordering Information

Device	Package	Shipping
SDURD1560	DPAK (Pb-Free)	2500pcs / reel

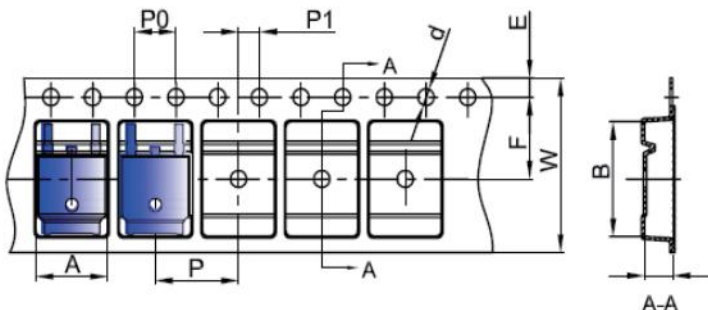
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel Packaging specification.

Marking Diagram


Where XXXXX is YYWWL

SDUR = Device Type
D = Package type
15 = Forward Current (15A)
60 = Reverse Voltage (600V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification DPAK


SYMBOL	Millimeters	
	Min.	Max.
A	6.80	7.00
B	10.40	10.60
C	2.60	2.80
d	Φ1.45	Φ1.65
E	1.65	1.85
F	7.40	7.60
P0	3.90	4.10
P	7.90	8.10
P1	1.90	2.10
W	15.90	16.30



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